

FOR IMMEDIATE RELEASE
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Addition to MMIC design team further enhances Nitronex's ability to push the technical limits of GaN technology...

Nitronex Names Principal MMIC Engineer

Durham, N.C. (April 29, 2008) — Nitronex, an innovative developer and manufacturer of high-performance GaN-on-Si RF power transistors for the wireless infrastructure, broadband, and military markets, has named Dr. Thomas A. Winslow as Principal Monolithic Microwave Integrated Circuit (MMIC) Engineer. Dr. Winslow has more than 15 years of industry experience in microwave circuit design.

“The Nitronex GaN-on-silicon process is uniquely positioned to combine the high performance of GaN technology with low cost silicon substrates to achieve new levels of integration and performance,” said Dr. Thomas Winslow. “I am excited to join Nitronex and have the opportunity to develop new and ground breaking GaN-based MMICs.”

During his 15 years at ITT-GTC and Tyco Electronics / M/A-Com, Dr. Thomas Winslow served as a Principal Member of the Technical Staff, Principal Engineer, and most recently, Senior Principal Engineer. He holds eight patents with three additional patents pending, has authored more than 20 technical papers and is a reputable member of the *International Journal of RF and Microwave Computer-Aided Engineering* editorial board. Dr. Winslow is also a Senior Member of the Institute of Electrical and Electronics Engineers.

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“The addition of an industry veteran like Dr. Winslow to our MMIC design team further enhances our ability to push the technical limits of our technology,” said Dr. Isik C. Kizilyalli, VP of Engineering. “Dr. Winslow will develop MMIC products to address challenges that our customers face and provide solutions not previously achievable without GaN-on-silicon technology.”

Dr. Winslow received his doctorate, master and undergraduate degrees from North Carolina State University.

For more information about GaN-on-Si manufacturing technology, contact Nitronex at 2305 Presidential Drive, Durham, NC 27703; call 919-807-9100; or e-mail info@nitronex.com.

About Nitronex

Specializing in the development and manufacturing of gallium nitride (GaN) RF power devices, Nitronex is the global leader in high-performance GaN-on-silicon (GaN-on-Si) RF power transistors for the commercial wireless infrastructure, broadband and military markets. Based on its patented SIGANTIC[®] process — gallium nitride on silicon technology — Nitronex is at the forefront of commercializing GaN technology for RF applications. The company’s ability to combine the disciplines of material growth, wafer processing, device design, and wireless applications knowledge is unique to the industry.

Nitronex was founded in 1999 by graduates of the wide bandgap program at North Carolina State University and is headquartered in Durham, North Carolina. It holds 19 patents with 19 others pending.

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